

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	870	(hydrophobic) with (semiconductor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/26 10:01
L2	545	(photoresist or photo-resist) with (hydrophobic)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/26 10:21
L3	58	1 and 2	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/26 10:13
L4	301	(etch\$3 or remov\$3) with (hydrophobic near layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/26 10:18
L5	23	2 and 4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/26 10:14
L6	834	(etch\$3 or remov\$3 or pattern\$3) same (hydrophobic near layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/26 10:19
L7	49	2 and 6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/26 10:19
L8	923	(photoresist or photo-resist) same (hydrophobic)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/26 10:22
L9	77	6 and 8	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/26 10:22

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L1	117252	(etch\$3 or remov\$3 or pattern\$3) with (photoresist or photo-resist)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/26 10:29
L2	251	1 and (hydrophobic near layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/26 10:35
L3	127	2 and (etch\$3 or pattern\$3 or remov\$3) with (hydrophobic)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/26 10:36
L4	2	"6342448".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/26 10:33
L5	779	1 and (hydrophobic or barc) near (layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/26 10:36
L6	779	1 and 5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/26 10:36
L7	554	6 and (etch\$3 or pattern\$3 or remov\$3) with (hydrophobic or barc)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/26 10:36